

IN THE CLAIMS:

Please amend the claims as follows:

1. (Previously Presented) A film deposition method comprising:
 - a first step of preparing a fluid that has organic metal as a main component which precipitates a film deposition material using pyrolytic decomposition, wherein the fluid comprises an aliphatic saturated hydrocarbon solvent and the organic metal is a copper diketonate;
 - a second step of applying the fluid onto a to-be-processed body at a temperature within the non-reactive range of the organic metal; and
 - a third step of heating the to-be-processed body to a second temperature, and causing a pyrolytic decomposition reaction of the organic metal throughout the fluid that is applied onto the to-be-processed body to occur to form a copper film on the to-be-processed body.
6. (Previously Presented) The film deposition method in claim 1, wherein the to-be-processed body is a semiconductor wafer.
11. (Currently Amended) A film deposition method comprising:
 - a first step of preparing a fluid that has organic metal as a main component which precipitates a film deposition material using pyrolytic decomposition, wherein the organic metal is selected from the group consisting of (hfac)Cu(tmvs) and (hfac)Cu()(hfac)Cu(teovs) and the fluid further comprises an aliphatic saturated hydrocarbon solvent;
 - a second step of applying the fluid onto a to-be-processed body at a temperature within the non-reactive range of the organic metal; and
 - a third step of heating the to-be-processed body to a second temperature, and causing a pyrolytic decomposition reaction of the organic metal throughout the fluid that is applied onto the to-be-processed body to occur to form a copper film on the to-be-processed body.

12. (Previously Presented) The film deposition method in claim 11, wherein the to-be-processed body is a semiconductor wafer.
13. (Previously Presented) A film deposition method comprising:
 - a first step of preparing a fluid that has organic metal as a main component which precipitates a film deposition material using pyrolytic decomposition, wherein the fluid further comprises an aliphatic saturated hydrocarbon solvent;
 - a second step of applying the fluid onto a to-be-processed body at a temperature within the non-reactive range of the organic metal; and
 - a third step of heating the to-be-processed body to a second temperature, and causing a pyrolytic decomposition reaction of the organic metal throughout the fluid that is applied onto the to-be-processed body to occur to form a film on the to-be-processed body.
14. (Previously Presented) The film deposition method in claim 13, wherein the organic metal is a copper diketonate.
15. (Previously Presented) The film deposition method in claim 14, wherein the copper diketonate is selected from the group consisting of (hfac) $\text{Cu}(\text{tmvs})$ and (hfac) $\text{Cu}(\text{teovs})$.
16. (Previously Presented) The film deposition method in claim 15, wherein copper is deposited as a film.
17. (Previously Presented) The film deposition method in claim 16, wherein the to-be-processed body is a semiconductor wafer.